

Description

The MOSFET provide the best combination of fast switching , low on-resistance and cost-effectiveness.

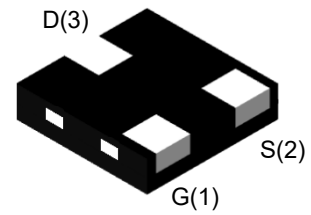
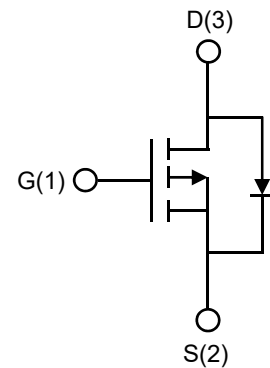
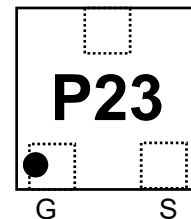
MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)(Typ)$	$I_D(A)$
-20	53 @ $V_{GS} = -4.5V$	-4.0
	67 @ $V_{GS} = -2.5V$	

Feature

- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Applications

- PWM applications
- Load switch
- Power management


**DFN1212-3L
(Bottom View)**

**Circuit Diagram
D**

Marking (Top View)
Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 12	V
Drain Current-Continuous ¹⁾	$T_C=25^\circ C$	I_D	-4.0	A
	$T_C=100^\circ C$		-2.5	
Pulsed Drain Current ²⁾		I_{DM}	-15	A
Total Power Dissipation ³⁾		P_D	1.5	W
Avalanche Current ⁴⁾		I_{AS}	-6.7	A
Avalanche Energy ⁴⁾		E_{AS}	11.4	mJ
Thermal Resistance , Junction-to-Case ⁵⁾		$R_{\theta JC}$	13.2	$^\circ C/W$
Thermal Resistance , Junction-to-Ambient ⁵⁾		$R_{\theta JA}$	81.9	$^\circ C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.45	-0.66	-0.9	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5V, I_D = -1A$	-	53	85	m Ω
		$V_{GS} = -2.5V, I_D = -1A$	-	67	100	
Dynamic Characteristics⁶⁾						
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V,$ $f = 1.0MHz$	-	328	-	pF
Output Capacitance	C_{oss}		-	39	-	
Reverse Transfer Capacitance	C_{rss}		-	37	-	
Switching Characteristics⁶⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = -10V, V_{GS} = -4.5V,$ $R_G = 6\Omega, I_D = -1A$	-	19	-	ns
Turn-on Rise Time	t_r		-	34	-	
Turn-Off Delay Time	$t_{d(off)}$		-	36	-	
Turn-Off Fall Time	t_f		-	23	-	
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V,$ $I_D = -1A$	-	3.1	-	nC
Gate-Source Charge	Q_{gs}		-	0.9	-	
Gate-Drain Charge	Q_{gd}		-	1.0	-	
Gate Resistance	R_g	f=1MHz, Open Drain	-	12	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = -1A$	-	-0.8	-1.2	V

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J_Max}=150^\circ C$).
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. This single-pulse measurement was taken under the following condition ($L=0.5mH, V_{GS}=-4.5V, V_{DS}=-20V$)while it's value is limited by $T_{J_Max}=150^\circ C$.
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
6. Guaranteed by design, not subject to production.

Typical Characteristics

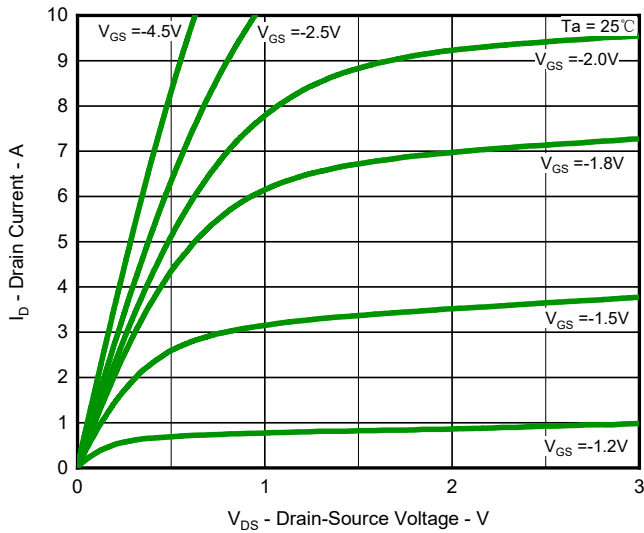


Fig.1 Output Characteristics

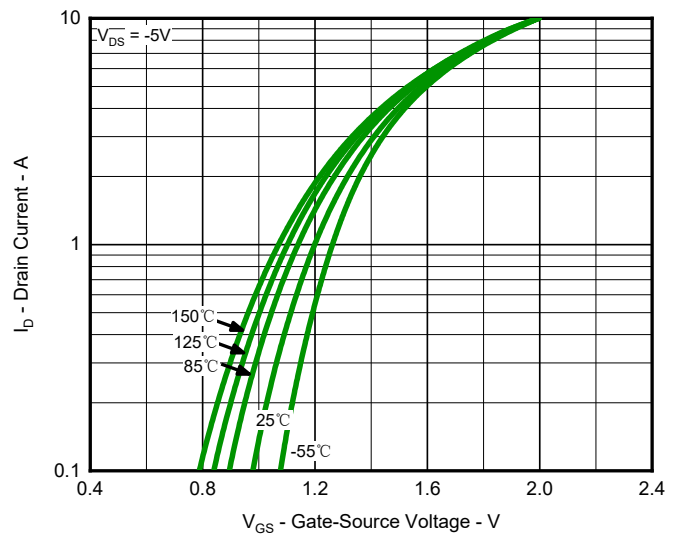


Fig.2 Typical Transfer Characteristic

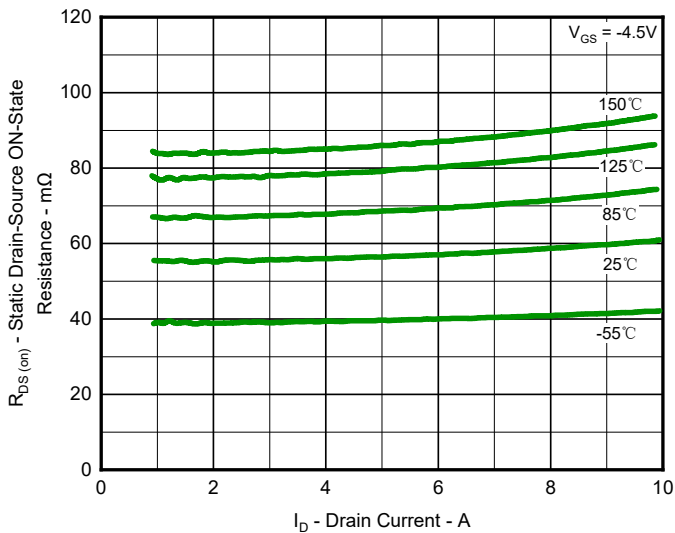


Fig.3 Typical On-Resistance vs Drain Current and Temperature

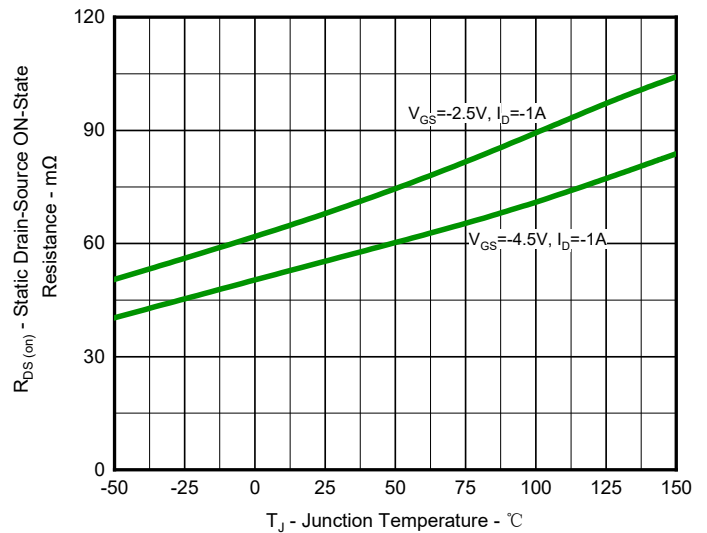


Fig.4 On-Resistance Variation with Temperature

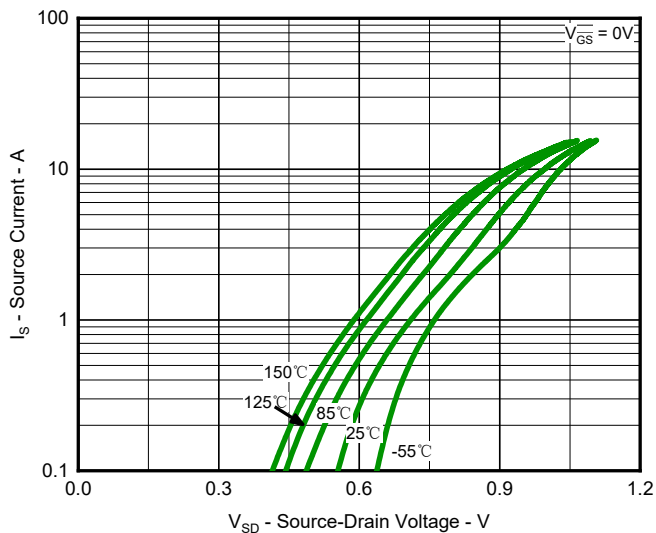


Fig.5 Diode Forward Voltage vs. Current

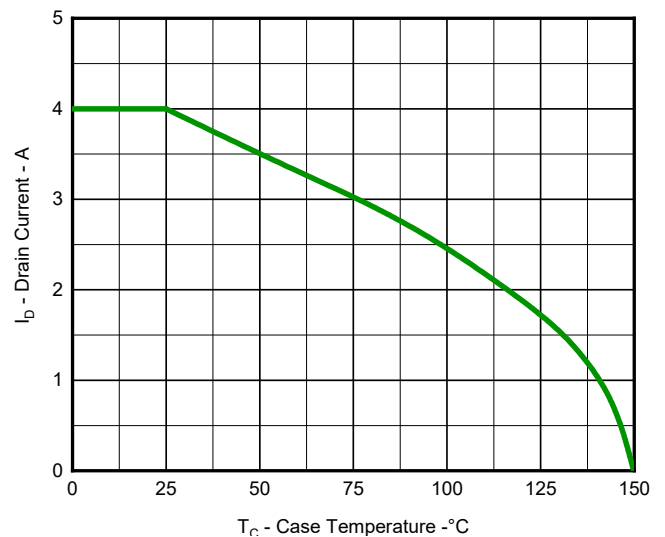


Fig.6 Maximum Drain Current vs. Case Temperature

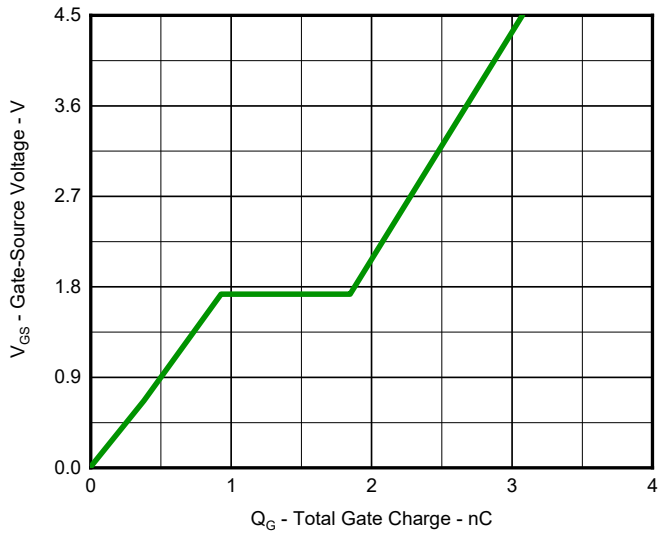


Fig.7 Gate Charge Characteristics

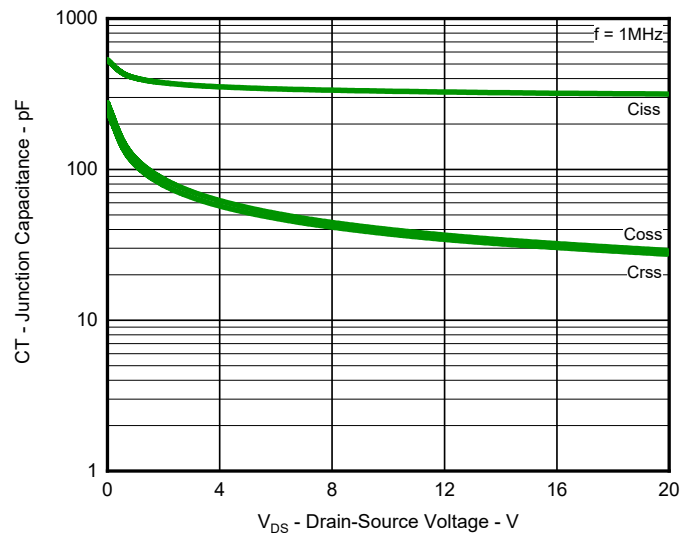


Fig.8 Typical Junction Capacitance

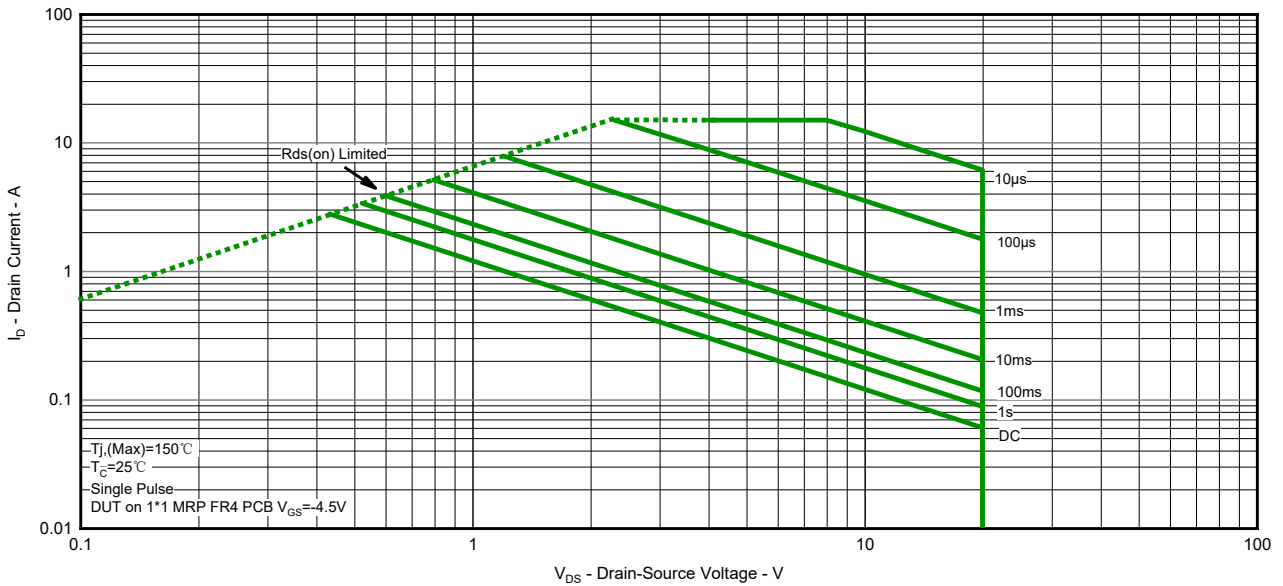


Fig.9 Safe Operation Area

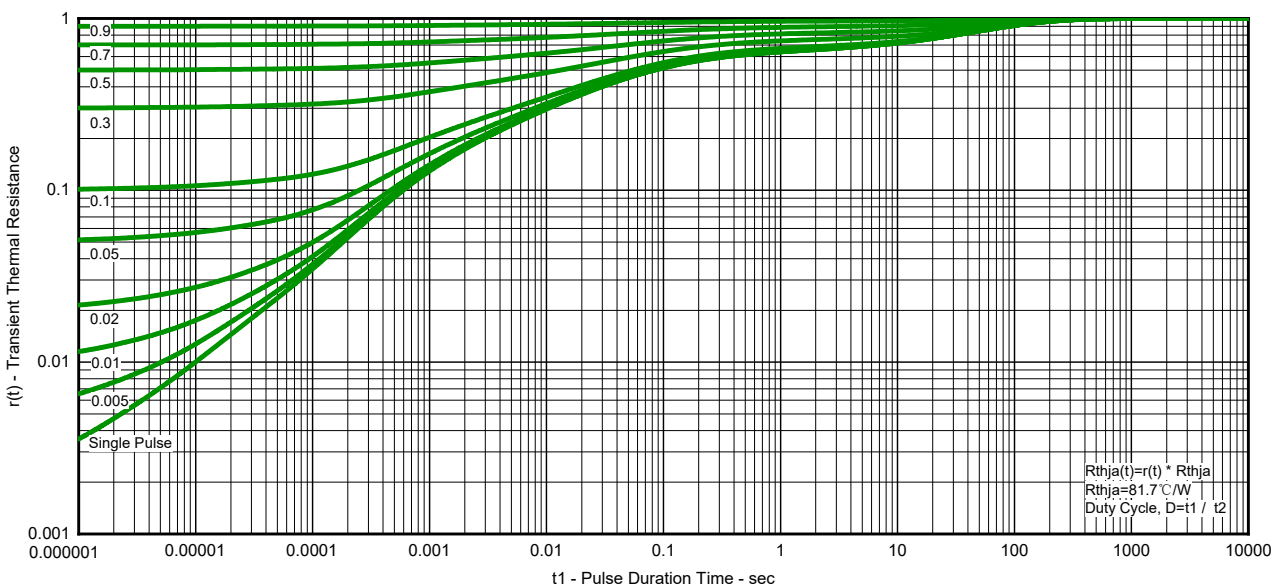
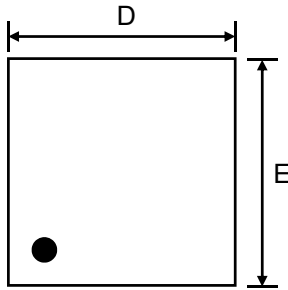
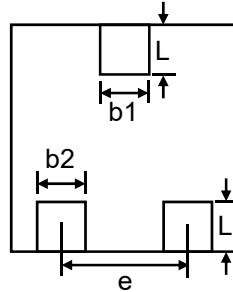


Fig.10 Transient Thermal Resistance

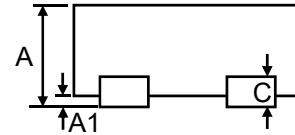
Product Dimension (DFN1212-3L)



Top View



Bottom View



Side View

Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.45	0.55	0.018	0.022
A1	0.00	0.05	0.000	0.002
b1	0.27	0.37	0.011	0.015
b2	0.25	0.35	0.010	0.014
C	0.152 Ref.		0.006 Ref.	
D	1.15	1.25	0.045	0.049
E	1.15	1.25	0.045	0.049
L	0.30	0.40	0.012	0.016
e	0.75 Ref.		0.030 Ref.	

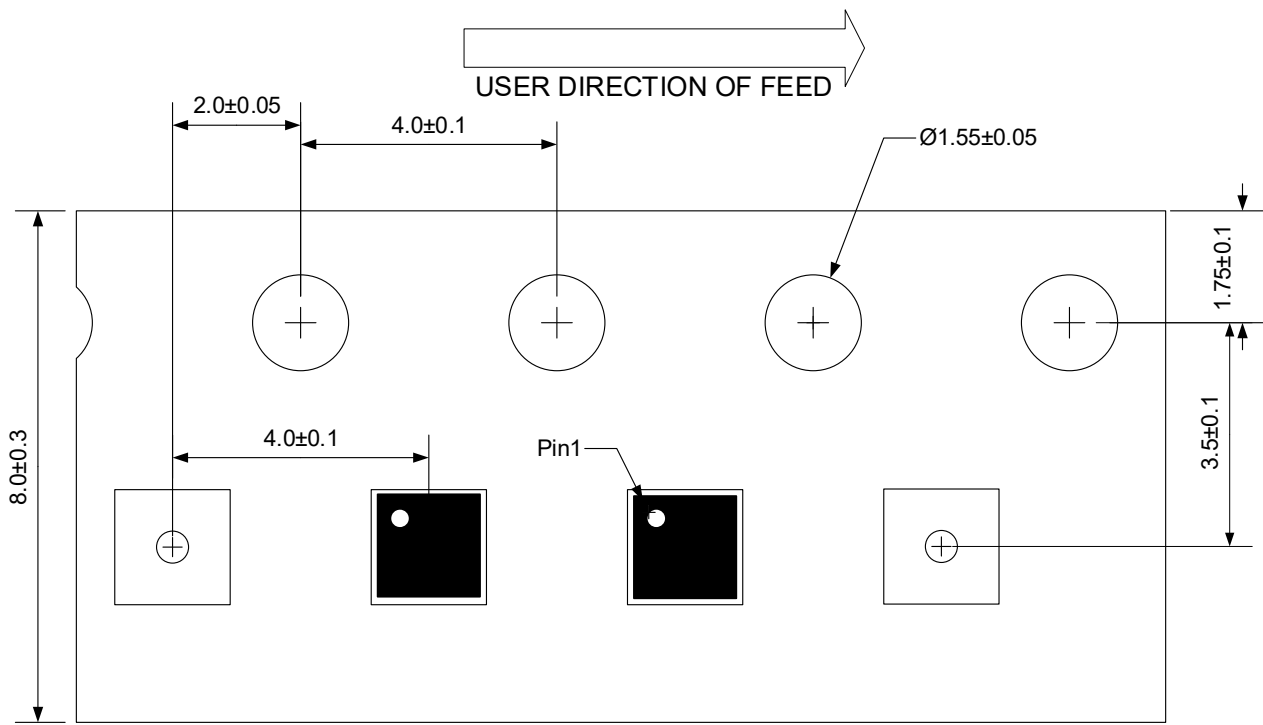
P-Channel MOSFET

PPM3GN20V3

Ordering information


Device	Package	Reel	Shipping
PPM3GN20V3	DFN1212-3L	7"	5000 / Tape & Reel

Load with information



Unit:mm


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